

2SB0788 (2SB788)

Silicon PNP epitaxial planar type

For high breakdown voltage low-noise amplification

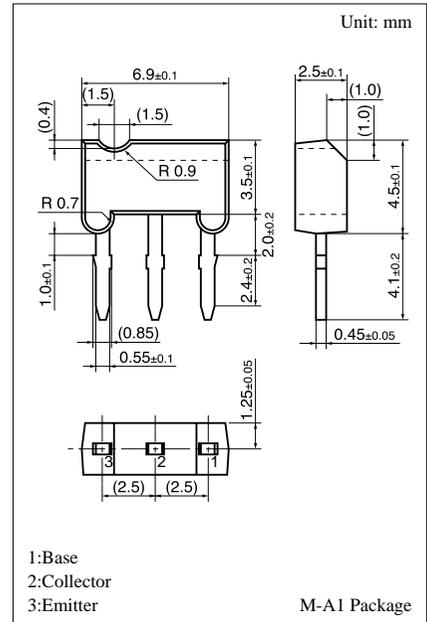
Complementary to 2SD0958 (2SD958)

Features

- High collector to emitter voltage V_{CEO} .
- Low noise voltage NV.
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board.

Absolute Maximum Ratings (Ta=25°C)

| Parameter | Symbol | Ratings | Unit |
|------------------------------|-----------|------------|------|
| Collector to base voltage | V_{CBO} | -120 | V |
| Collector to emitter voltage | V_{CEO} | -120 | V |
| Emitter to base voltage | V_{EBO} | -7 | V |
| Peak collector current | I_{CP} | -50 | mA |
| Collector current | I_C | -20 | mA |
| Collector power dissipation | P_C | 400 | mW |
| Junction temperature | T_j | 150 | °C |
| Storage temperature | T_{stg} | -55 ~ +150 | °C |



Electrical Characteristics (Ta=25°C)

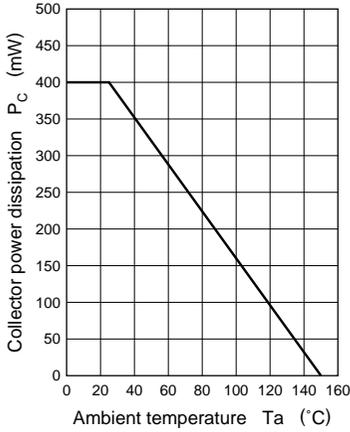
| Parameter | Symbol | Conditions | min | typ | max | Unit |
|---|---------------|---|------|-----|------|------|
| Collector cutoff current | I_{CBO} | $V_{CB} = -50V, I_E = 0$ | | | -100 | nA |
| | I_{CEO} | $V_{CE} = -50V, I_B = 0$ | | | -1 | μA |
| Collector to base voltage | V_{CBO} | $I_C = -10\mu A, I_E = 0$ | -120 | | | V |
| Collector to emitter voltage | V_{CEO} | $I_C = -1mA, I_B = 0$ | -120 | | | V |
| Emitter to base voltage | V_{EBO} | $I_E = -10\mu A, I_C = 0$ | -7 | | | V |
| Forward current transfer ratio | h_{FE}^* | $V_{CE} = -5V, I_C = -2mA$ | 180 | | 700 | |
| Collector to emitter saturation voltage | $V_{CE(sat)}$ | $I_C = -20mA, I_B = -2mA$ | | | -0.6 | V |
| Transition frequency | f_T | $V_{CB} = -5V, I_E = 2mA, f = 200MHz$ | | 150 | | MHz |
| Noise voltage | NV | $V_{CE} = 40V, I_C = -1mA, G_V = 80dB, R_g = 100k\Omega, \text{Function} = \text{FLAT}$ | | | 150 | mV |

* h_{FE} Rank classification

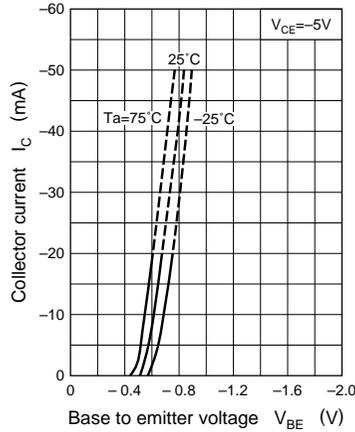
| Rank | R | S | T |
|----------|-----------|-----------|-----------|
| h_{FE} | 180 ~ 360 | 260 ~ 520 | 360 ~ 700 |

Note.) The Part number in the Parenthesis shows conventional part number.

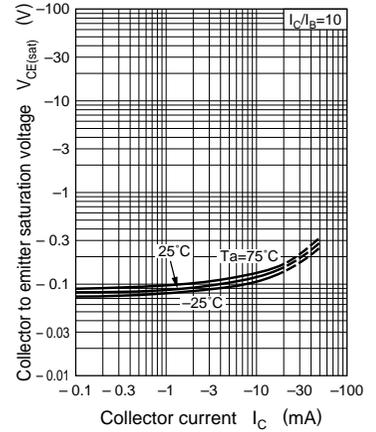
$P_C - T_a$



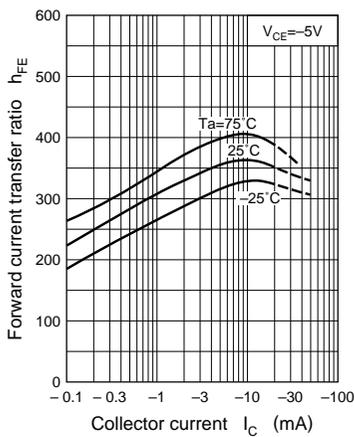
$I_C - V_{BE}$



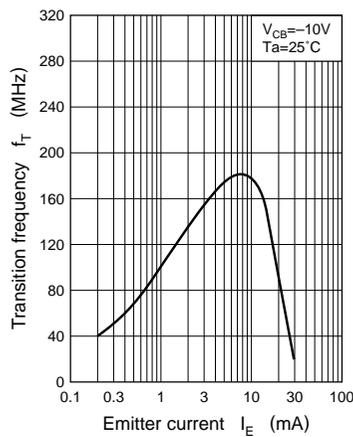
$V_{CE(sat)} - I_C$



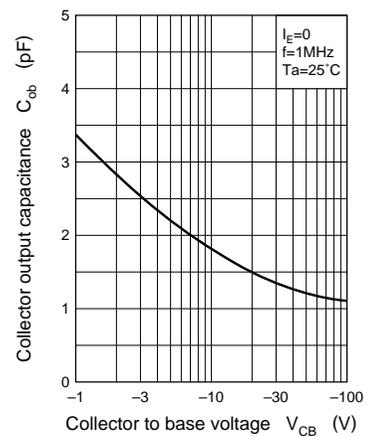
$h_{FE} - I_C$



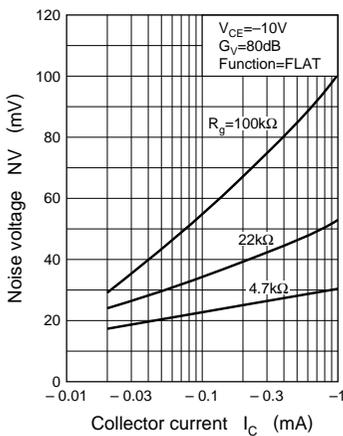
$f_T - I_E$



$C_{ob} - V_{CB}$



$NV - I_C$



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